

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	Package	I <sub>D</sub> max T <sub>A</sub> = +25°C
-40V	33mΩ @ V <sub>GS</sub> = -10V	U-DFN2020-6 (Type E)	-6A
	50mΩ @ V <sub>GS</sub> = -4.5V		-4.9A

## Description

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- General Purpose Interfacing Switch
- Load Switching
- Battery Management Application
- Power Management Functions

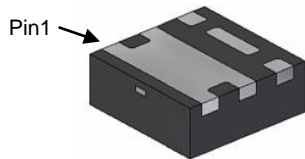
## Features

- 0.6mm Profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Low On-Resistance
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

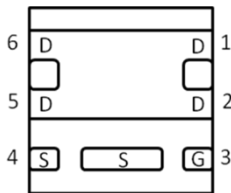
## Mechanical Data

- Case: U-DFN2020-6 (Type E)
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 <sup>(e4)</sup>
- Weight: 0.0065 grams (Approximate)

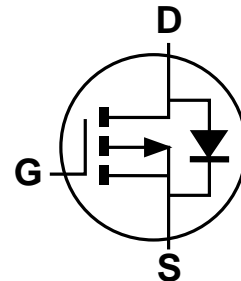
U-DFN2020-6 (Type E)



Bottom View



Pin Out  
Bottom View



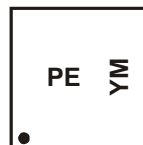
Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Quantity Per Reel
DMP4047LFDE-7	PE	7	3,000
DMP4047LFDE-13	PE	13	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



PE = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: E = 2017)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2011	...	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	Y	...	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-40	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-3.3 -2.6	A
	t < 5s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-5.3 -4.2	A
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-6.0 -4.8	A
	t < 5s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-9.5 -7.6	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-40	A
Maximum Body Diode Continuous Current			I <sub>S</sub>	-3	A

**Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.7	W
	T <sub>A</sub> = +70°C		0.42	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	180	°C/W
	t < 5s		76	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.1	W
	T <sub>A</sub> = +70°C		1.3	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	58	°C/W
	t < 5s		25	
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	10.2	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1	µA	V <sub>DS</sub> = -40V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	—	-2.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	26	33	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -4.4A
			36	50		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.7A
Forward Transfer Admittance	Y <sub>fs</sub>	—	5.2	—	S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -4.4A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.75	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -3.9A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	1382	—	pF	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	103	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	81	—	pF	
Gate Resistance	R <sub>g</sub>	—	7.7	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	11.2	—	nC	V <sub>DS</sub> = -20V, I <sub>D</sub> = -4.9A
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	23.2	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	3.3	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	3.9	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	18.4	—	ns	V <sub>DS</sub> = -20V, I <sub>D</sub> = -3.9A V <sub>GS</sub> = -4.5V, R <sub>G</sub> = 1Ω
Turn-On Rise Time	t <sub>R</sub>	—	28.2	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	38.8	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	28.6	—	ns	
Reverse Recovery Time	t <sub>RR</sub>	—	15.4	—	ns	I <sub>F</sub> = -3.9A, di/dt = 100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	5.4	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate
  - Short duration pulse test used to minimize self-heating effect
  - Guaranteed by design. Not subject to production testing

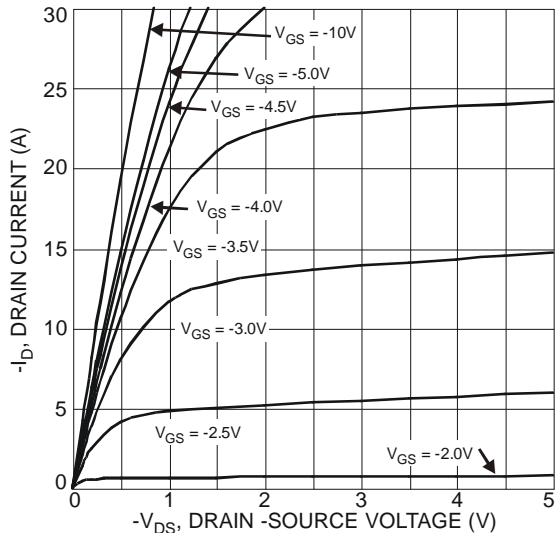


Fig. 1 Typical Output Characteristics

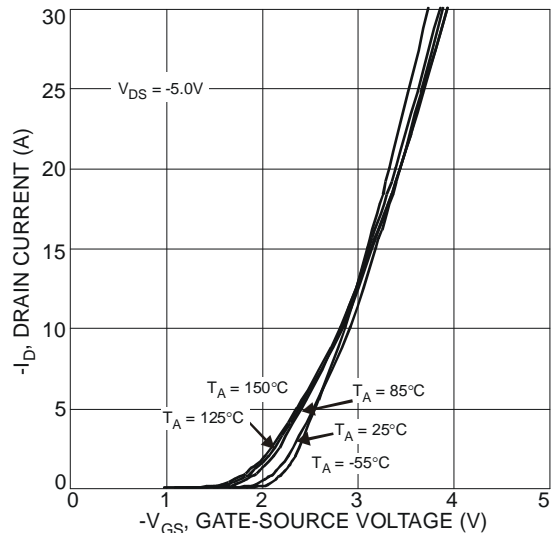


Fig. 2 Typical Transfer Characteristics

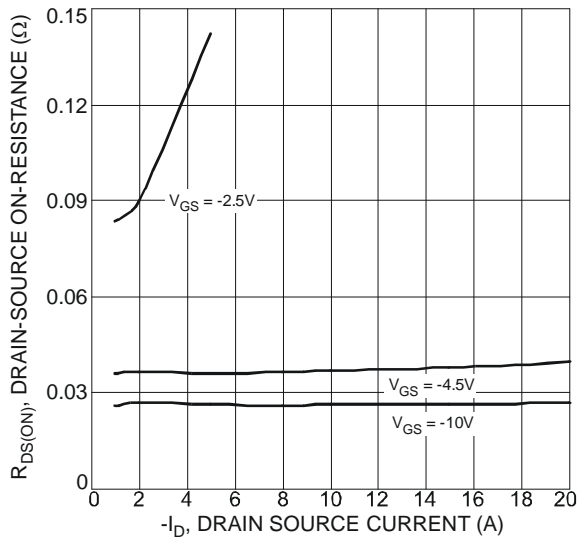


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

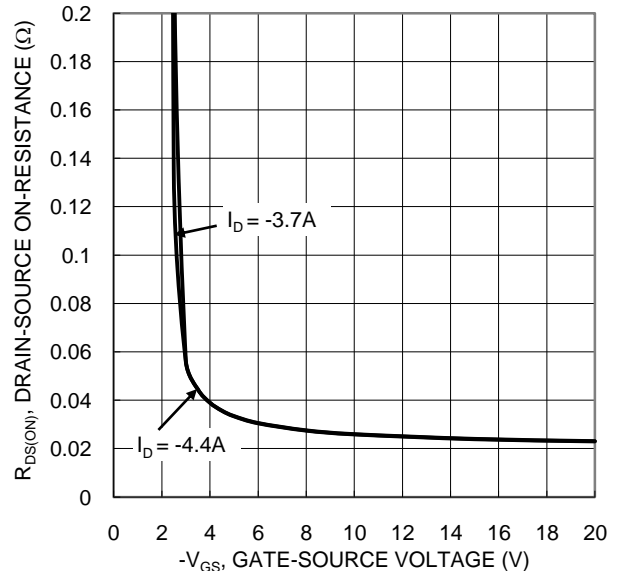


Fig. 4 Typical On-Resistance vs Gate Voltage

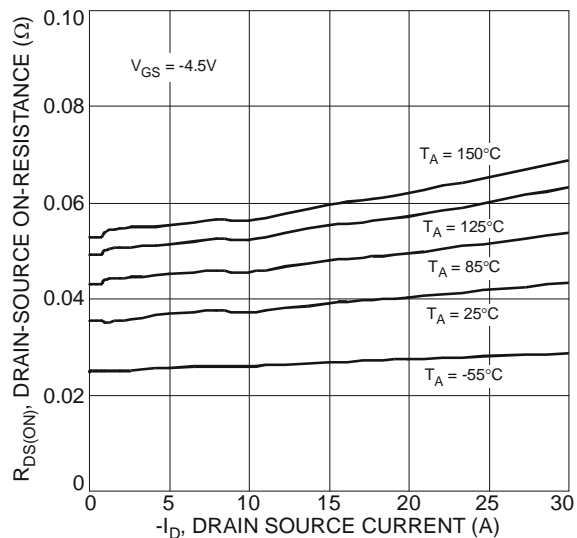


Fig. 5 Typical On-Resistance vs. Drain Current and Temperature

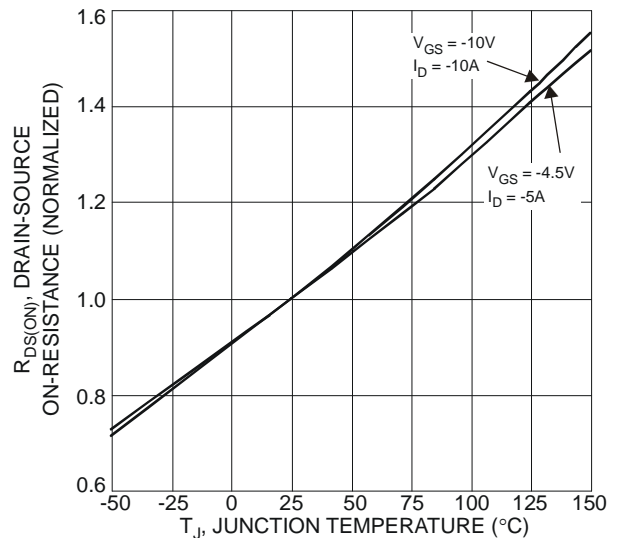


Fig. 6 On-Resistance Variation with Temperature

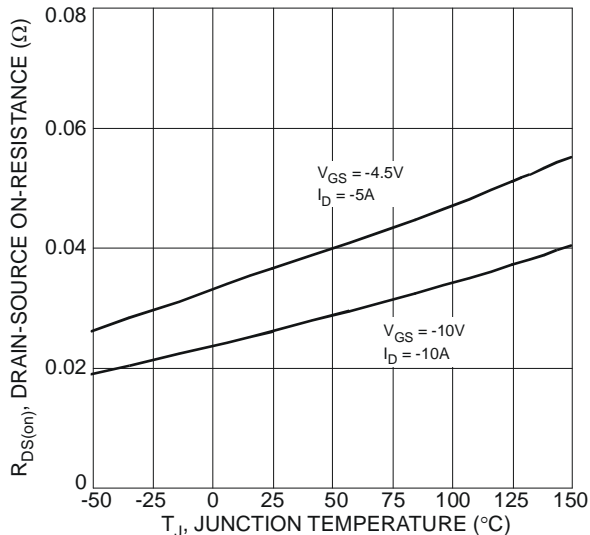


Fig. 7 On-Resistance Variation with Temperature

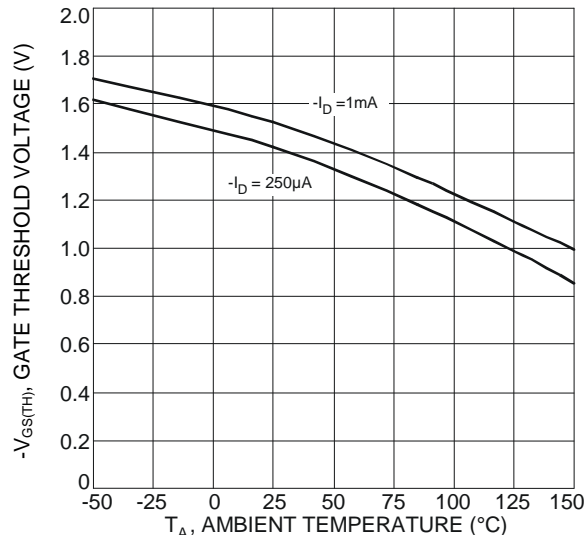


Fig. 8 Gate Threshold Variation vs. Ambient Temperature

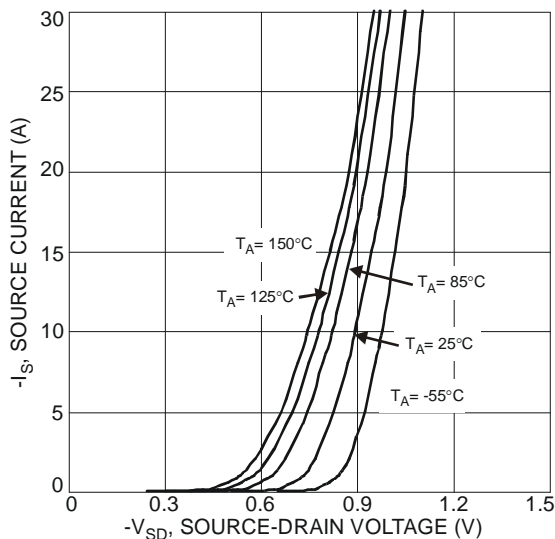


Fig. 9 Diode Forward Voltage vs. Current

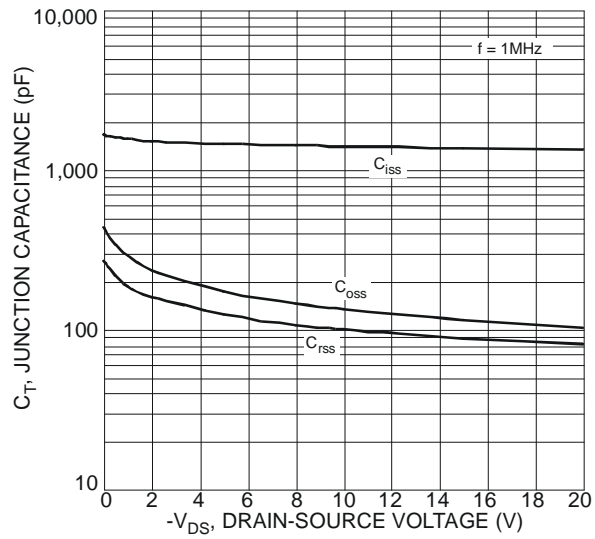


Fig. 10 Typical Junction Capacitance

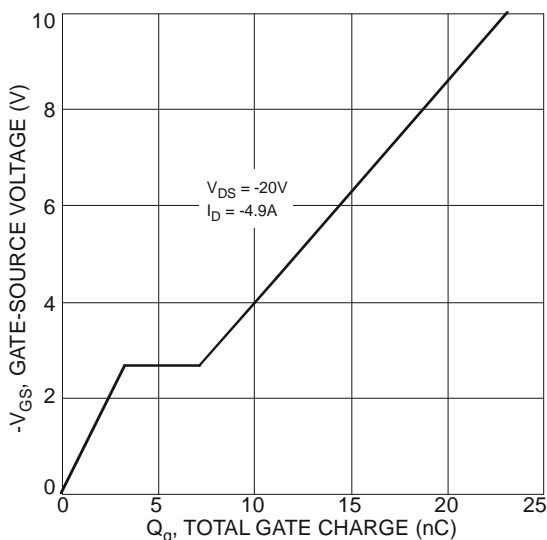


Fig. 11 Gate-Charge Characteristics

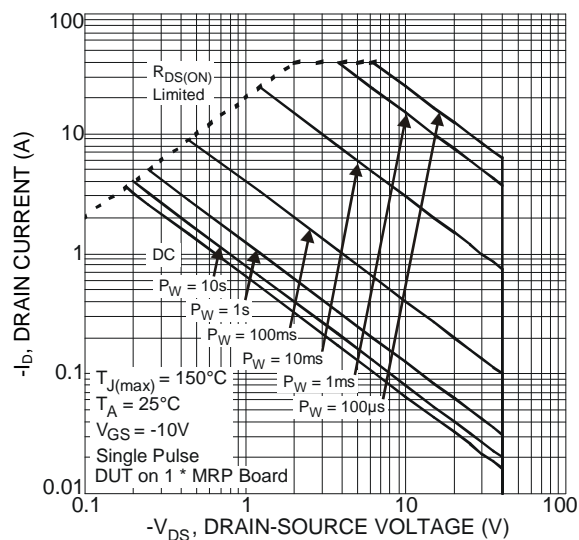
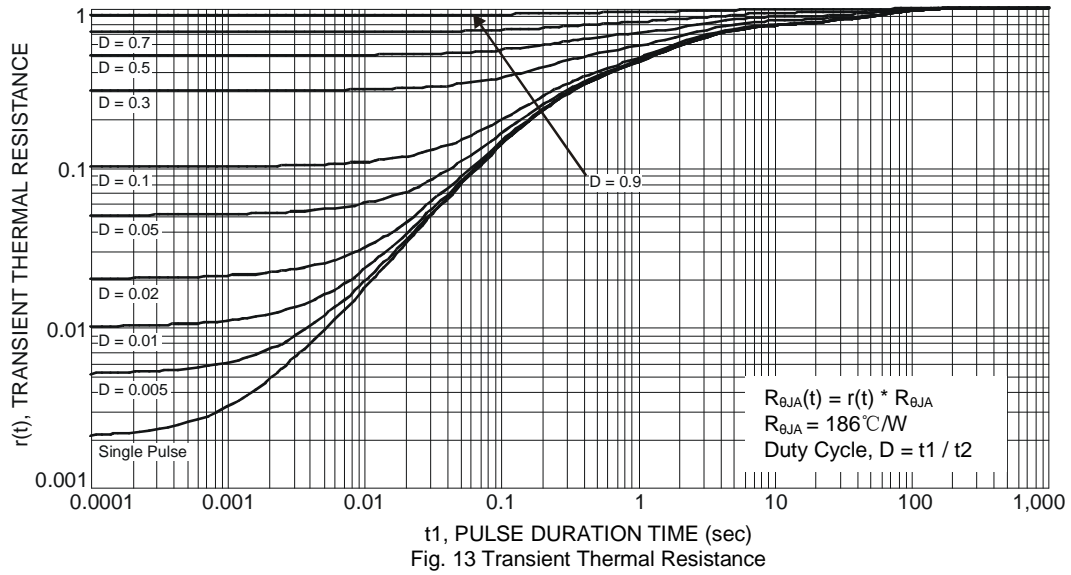


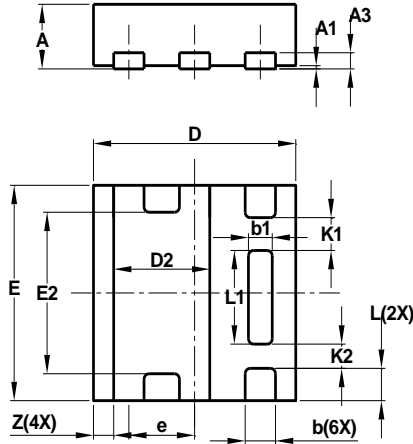
Fig. 12 SOA, Safe Operation Area



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type E)**

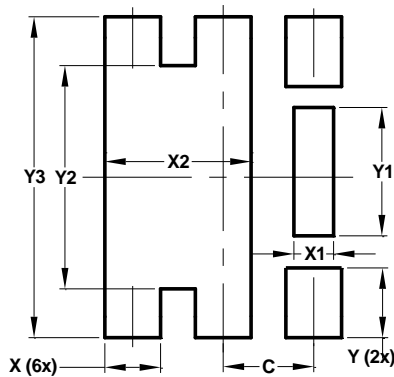


U-DFN2020-6 Type E			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	—	—	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	—	—	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
K1	—	—	0.305
K2	—	—	0.225
Z	—	—	0.20
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type E)**



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

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